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Sheet 2 of 2

### Complete if Known

Application Number	TBA
Filing Date	Herewith
First Named Inventor	TAKEDA et al.
Group Art Unit	TBA
Examiner Name	TBA
Attorney Docket Number	KOJIM-448

### OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
S.T.L.	L	International Work Shop 157nm Lithography MIT-LL, Boston, MA, May 5, 1999	
	M	Kunz et al. "Outlook for 157 nm Resist Design," <i>J. Vac. Sci. Technol. B</i> 17(6), Nov/Dec 1999, pp. 3267-3272	
	N	Chiba et al., "157 nm Resist Materials: A Progress Report," <i>J. Photopolymer Science and Technology</i> , Vol. 13, No. 4 (2000) pp 657-664	
	O	Schmaljohann et al., "Fundamental Studies of Fluoropolymer Photoresists for 157 nm Lithography," <i>J. of Photopolymer Science Technology</i> , Vol., 13, No. 3 (2000) pp 451-458	
	P	Brunsvold et al., "Evaluation of a Deep UV Bilayer Resist for Sub-Half Micron Lithography," <i>SPIE Vol. 1925</i> (1993), pp. 377-387	
	Q	Hatakeyama et al., "Investigation of Discrimination Enhancement in Polysilsesquioxane Based Positive Resist for ArF Lithography" <i>SPIE Vol. 3333</i> , pp. 62-72	
	R	Blakeney et al., "Evaluation of Materials for 193-nm Lithography" <i>J. of Photopolymer Science and Technology</i> , Vol. 9, No. 3 (1996) pp 435-446	
	S	Kessel, et al., "novel Silicon-Containing Resists for EUV and 193 nm Lithography" <i>SPIE Vol. 3678</i> (1999), pp. 214-220	
	T	Lin et al., "A High Resolution 248 nm Bilayer Resist" <i>SPIE Vol. 3678</i> (1999) pp. 241250	
	U	Boardman et al., "Chemical Aspects of Silicon-Containing Bilayer Resists" <i>SPIE Vol. 3678</i> (1999) pp. 562-572	
	V	Kim et al., "Chemically amplified resist based on the methacrylate polymer with 2-trimethylsilyl-2-propyl ester protecting group" <i>SPIE Vol. 3678</i> (1999) pp 420-428	

Examiner  
Signature

*Li A. Lee*

Date  
Considered

9-25-03

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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